Product data sheet

1. General description

Dual common cathode power Schottky diode designed for high frequency switched mode power supplies in a TO220 plastic package.





2. Features and benefits

- Trench structure
- High junction temperature up to 150°C
- · Low forward voltage drop, negligible switching losses
- High efficiency

3. Applications

- · DC to DC converters
- Freewheeling diode
- · OR-ing diode
- · Switched mode power supply rectifier

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions Notes Values			Unit		
Absolute	maximum rating						
V_{RRM}	repetitive peak reverse 60 voltage						V
I _{F(AV)}	average forward current	$δ$ = 0.5 ; square-wave pulse; T_{mb} ≤ 116 °C; per diode; Fig. 1; Fig. 2; Fig. 3			15		
I _{O(AV)}	average output current	δ = 0.5 ; square-wave pulse; $T_{mb} \le 110$ °C; both diodes conducting		30			A
Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
Static ch	aracteristics						
V _F	forward voltage	$I_F = 15 \text{ A}; T_j = 25 \text{ °C}; \text{ per diode}; Fig. 6$		-	0.62	0.70	V
I _R	reverse current	$V_R = 60 \text{ V}; T_j = 25 \text{ °C}; \text{ per diode}; $ - 35 100 Fig. 7; Fig. 8				100	μA

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WN3S3060C

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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1	mb	
2	K	cathode		A1 A2
3	A2	anode 2		K sym125
mb	К	mounting base; connected to cathode		cymr2c

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WN3S3060C	TO220	WN3S3060CQ	Tube	50	SOT78	13-Jun-2008

7. Marking

Table 4. Marking codes

Type number	Marking codes
WN3S3060C	WN3S 3060C

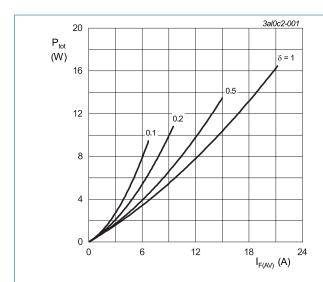
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

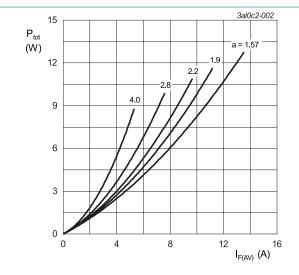
Symbol	Parameter	Conditions	Notes	Values	Unit
V_{RRM}	repetitive peak reverse voltage			60	V
V_{RWM}	crest working reverse voltage			60	V
V_R	reverse voltage	DC		60	V
I _{F(AV)}	average forward current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 116$ °C; per diode; Fig. 1; Fig. 2; Fig. 3		15	А
$I_{O(AV)}$	average output current	$δ$ = 0.5; square-wave pulse; $T_{mb} \le 110$ °C; both diodes conducting		30	А
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4		150	А
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode		165	А
T _{stg}	storage temperature			-40 to 150	°C
T _j	junction temperature		[1]	-40 to 150	°C

[1] The heat generated must be less than the thermal conductivity from Junction to Ambient: $dP_{tot}/dT_j < 1/R_{th(j-a)}$



 $I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$ $V_o = 0.485 \text{ V; } R_s = 0.0137 \text{ }\Omega$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode



a = form factor = $I_{F(RMS)} / I_{F(AV)}$ V_o = 0.485 V; R_s = 0.0137 Ω

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values; per diode

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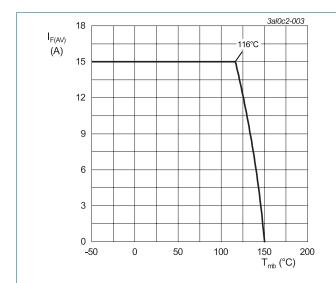


Fig. 3. Average forward current as a function of mounting base temperature; maximum values; per diode

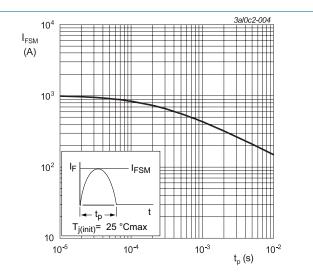


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values; per diode

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit
$R_{\text{th(j-mb)}}$	thermal resistance from junction to	per diode; Fig. 5		-	-	2.5	K/W
	mounting base	both diodes conducting		-	-	1.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air		-	60	-	K/W

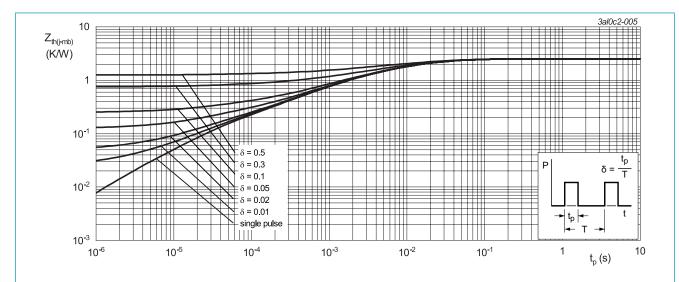


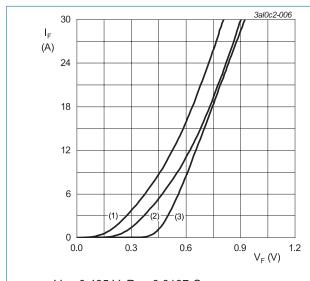
Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration; maximum values; per diode

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Notes	Min	Тур	Max	Unit		
Static cha	aracteristics								
V _F	forward voltage	I _F = 15 A; T _j = 25 °C; per diode; <u>Fig. 6</u>		-	0.62	0.70	V		
				I _F = 15 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.61	-	V
		I _F = 3 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.40	-	V		
		I _F = 3 A; T _j = 125 °C; per diode; <u>Fig. 6</u>		-	0.30	-	V		
I _R	reverse current	V _R = 60 V; T _j = 25 °C; per diode; Fig. 7; Fig. 8		-	35	100	μΑ		
		V _R = 60 V; T _j = 125 °C; per diode; Fig. 7; Fig. 8		-	20	100	mA		



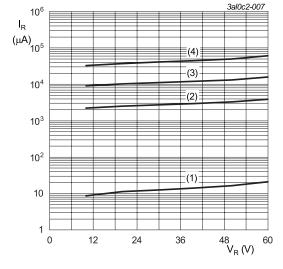
 V_o = 0.485 V; R_s = 0.0137 Ω

(1) T_i = 150 °C; typical values

(2) T_i = 150 °C; maximum values

(3) $T_i = 25$ °C; maximum values

Fig. 6. Forward current as a function of forward voltage; per diode



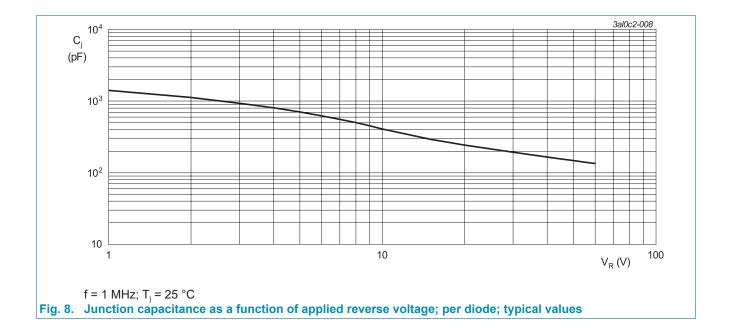
(1) T_i = 25 °C; typical values

(2) T_i = 100 °C; typical values

(3) $T_j = 125$ °C; typical values (4) $T_j = 150$ °C; typical values

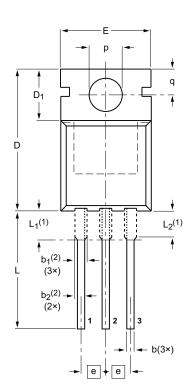
Fig. 7. Reverse leakage current as a function of reverse voltage; per diode; typical values

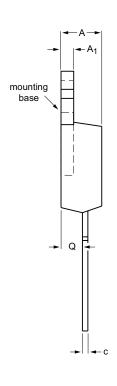
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11. Package outline







0 5 10 mm scale

DIMENSIONS (mm are the original dimensions)

UNIT	Α	A ₁	b	b ₁ ⁽²⁾	b ₂ ⁽²⁾	С	D	D ₁	E	е	L	L ₁ ⁽¹⁾	L ₂ ⁽¹⁾ max.	р	q	Q	
mm	4.7 4.1	1.40 1.25	0.9 0.6	1.6 1.0	1.3 1.0	0.7 0.4	16.0 15.2	6.6 5.9	10.3 9.7	2.54	15.0 12.8	3.30 2.79	3.0	3.8 3.5	3.0 2.7	2.6 2.2	

Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

OUTL	INE		REFER	ENCES	EUROPEAN	ISSUE DATE
VERS	ION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE
SOT	78		3-lead TO-220AB	SC-46	$ \ \ $	08-04-23 08-06-13

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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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